

INFORMATION DISCLOSURE CITATION IN AN APPLICATION			ATTY. DOCKET NO. 57454-224	SERIAL NO. 09/982,936		
(PTO-1449)			FED 15 2002 APPLICANT Hideto HIDAKA			
			FILING DATE October 22, 2001	GROUP 2818		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	
DL	5,732,016	3/24/1998	Chen et al. (Counterpart of Japanese Patent Laying-Open No. 2001-297579)			
DL	6,215,707	4/10/2001	Moyer (Counterpart of Japanese Publication No. 10-116489)			
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						Yes
DL	2001-297579	10/26/2000	Japan (w/ cover sheet)			
DL	10-116489	5/6/1998	Japan (w/ English Abstract)			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER	DATE CONSIDERED			4/02		

**EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)	ATTY. DOCKET NO. <b>57454-224</b>	SERIAL NO. 
APPLICANT <b>Hideto HIDAKA</b>		 j1046 U.S. PTO J109/982936 10/22/01
FILING DATE <b>October 22, 2001</b>		GROUP

## **U.S. PATENT DOCUMENTS**

## FOREIGN PATENT DOCUMENTS

**OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

DL	Scheuerlein, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell," ISSCC Digest of Technical Papers, TA7.2, 02/2000, pages 94-95, 128-129 and 409-410  Durlam, et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements," ISSCC Digest of Technical Papers, TA7.3, 02/2000, pages 96-97, 130-131 and 410-411.